bonding electrons on a surface of the thin film during the cooling solidification being terminated by hydrogen atoms in the hydrogen-containing atmosphere; and

positioning the introduction window relative to the thin film at a location resistant to adherence of components of the thin film when the high energy is supplied to the thin film.

25. (Four Times Amended) A method of forming a crystalline film, comprising:

forming a thin film on a substrate;

setting the thin film in a supply chamber of a high energy supply apparatus including a generation source for generating the high energy and the supply chamber for supplying the high energy to the thin film, the supply chamber including a wall and an introduction window provided in a portion of the wall, the introduction window introducing the high energy into the chamber;

crystallizing at least a surface layer of the thin film by supplying high energy to the thin film under a hydrogen-containing atmosphere, at least the surface layer of the thin film being melted by the high energy and crystallized by cooling solidification, and unpaired bonding electrons on a surface of the thin film during the cooling solidification being terminated by hydrogen atoms in the hydrogen-containing atmosphere; and

positioning the introduction window relative to the thin film so that a distance between the introduction window and the thin film being larger than a shortest distance between the wall and the thin film when the high energy is supplied to the thin film.

46. (Four Times Amended) A method of forming a crystalline film, comprising:

forming a thin film on a substrate; and

crystallizing at least a surface layer of the thin film by supplying high energy to the thin film under a hydrogen-containing atmosphere, at least the surface layer of the thin film is melted by the high energy and crystallized by cooling solidification, and unpaired